



PUMD10

50 V, 100 mA NPN/PNP resistor-equipped double transistor;
R1 = 2.2 k Ω , R2 = 47 k Ω

1 October 2022

Product data sheet

1. General description

NPN/PNP double Resistor-Equipped Transistor (RET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package.

PNP/PNP complement: PUMB10

NPN/NPN complement: PUMH10

2. Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs

3. Applications

- Low current peripheral driver
- Control of IC inputs
- Replaces general-purpose transistors in digital applications

4. Quick reference data

Table 1. Quick reference data

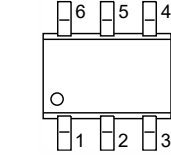
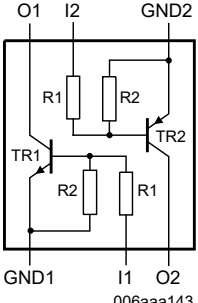
Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
Per transistor; for the PNP transistor (TR2) with negative polarity, where applicable							
V _{CEO}	collector-emitter voltage	open base	-	-	50	V	
I _O	output current		-	-	100	mA	
R1	bias resistor 1 (input)		[1]	1.54	2.2	2.86	k Ω
R2/R1	bias resistor ratio		[1]	17	21	26	

[1] See section "Test information" for resistor calculation and test conditions.

50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 2.2 k Ω , R2 = 47 k Ω

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	GND1	GND (emitter) TR1	 <p>TSSOP6 (SOT363)</p>	
2	I1	input (base) TR1		
3	O2	output (collector) TR2		
4	GND2	GND (emitter) TR2		
5	I2	input (base) TR2		
6	O1	output (collector) TR1		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PUMD10	TSSOP6	plastic, surface-mounted package; 6 leads; 0.65 mm pitch; 2.1 mm x 1.25 mm x 0.95 mm body	SOT363

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PUMD10	D%0

[1] % = placeholder for manufacturing site code

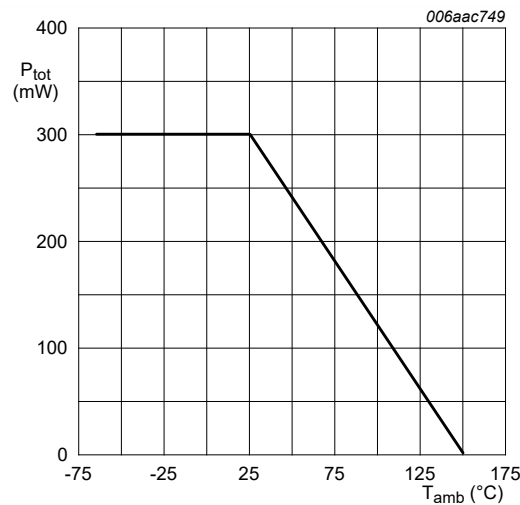
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transistor; for the PNP transistor (TR2) with negative polarity, where applicable					
V _{CBO}	collector-base voltage	open emitter	-	50	V
V _{CEO}	collector-emitter voltage	open base	-	50	V
V _{EBO}	emitter-base voltage	open collector	-	5	V
V _I	input voltage	positive (input voltage TR1)	-	12	V
		negative (Input voltage TR1)	-	-5	V
		positive (input voltage TR2)	-	5	V
		negative (Input voltage TR2)	-	-12	V
I _O	output current		-	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	200	mW
Per device					
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	300	mW
T _j	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	150	°C
T _{stg}	storage temperature		-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



FR4 PCB, single-sided, 35 μm copper, tin-plated and standard footprint

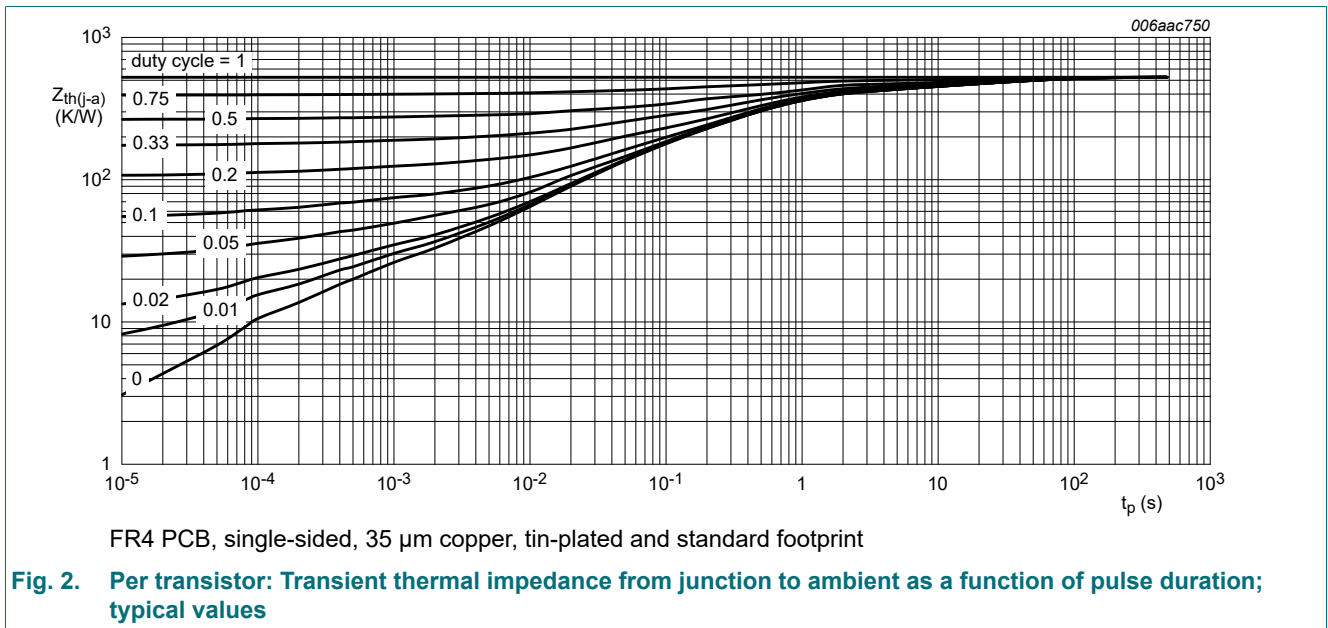
Fig. 1. Per device: Power derating curve

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Per transistor							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	625	K/W
Per device							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	417	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



10. Characteristics

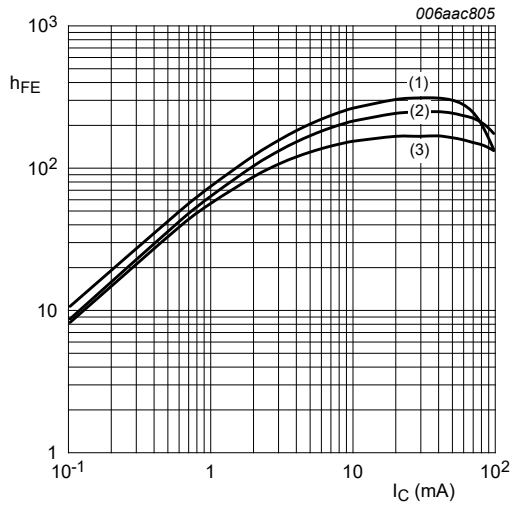
Table 7. Characteristics

$T_{amb} = 25\text{ °C}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Per transistor; for the PNP transistor (TR2) with negative polarity, where applicable						
$V_{(BR)CBO}$	collector-base breakdown voltage	$I_C = 100\ \mu\text{A}$; $I_E = 0\ \text{A}$	50	-	-	V
$V_{(BR)CEO}$	collector-emitter breakdown voltage	$I_C = 2\ \text{mA}$; $I_B = 0\ \text{A}$	50	-	-	V
I_{CBO}	collector-base cut-off current	$V_{CB} = 50\ \text{V}$; $I_E = 0\ \text{A}$	-	-	100	nA
I_{CEO}	collector-emitter cut-off current	$V_{CE} = 30\ \text{V}$; $I_B = 0\ \text{A}$	-	-	100	nA
		$V_{CE} = 30\ \text{V}$; $I_B = 0\ \text{A}$; $T_J = 150\text{ °C}$	-	-	5	μA
I_{EBO}	emitter-base cut-off current	$V_{EB} = 5\ \text{V}$; $I_C = 0\ \text{A}$	-	-	180	μA
h_{FE}	DC current gain	$V_{CE} = 5\ \text{V}$; $I_C = 10\ \text{mA}$	100	-	-	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 5\ \text{mA}$; $I_B = 0.25\ \text{mA}$	-	-	100	mV
$V_{I(off)}$	off-state input voltage	$V_{CE} = 5\ \text{V}$; $I_C = 100\ \mu\text{A}$	-	0.6	0.5	V
$V_{I(on)}$	on-state input voltage	$V_{CE} = 0.3\ \text{V}$; $I_C = 5\ \text{mA}$	1.1	0.75	-	V
R1	bias resistor 1 (input)		[1]	2.2	2.86	kΩ
R2/R1	bias resistor ratio		[1]	21	26	
TR1 (NPN)						
C_c	collector capacitance	$V_{CB} = 10\ \text{V}$; $I_E = 0\ \text{A}$; $i_e = 0\ \text{A}$; $f = 1\ \text{MHz}$	-	-	2.5	pF
f_T	transition frequency	$V_{CE} = 5\ \text{V}$; $I_C = 10\ \text{mA}$; $f = 100\ \text{MHz}$	[2]	230	-	MHz
TR2 (PNP)						
C_c	collector capacitance	$V_{CB} = 10\ \text{V}$; $I_E = 0\ \text{A}$; $i_e = 0\ \text{A}$; $f = 1\ \text{MHz}$	-	-	3	pF
f_T	transition frequency	$V_{CE} = 5\ \text{V}$; $I_C = 10\ \text{mA}$; $f = 100\ \text{MHz}$	[2]	180	-	MHz

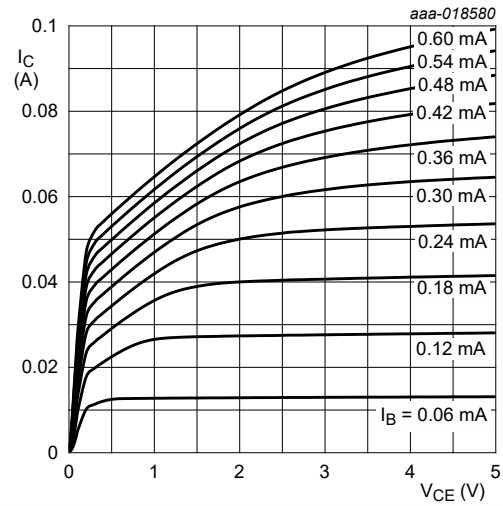
[1] See section "Test information" for resistor calculation and test conditions.

[2] Characteristics of built-in transistor



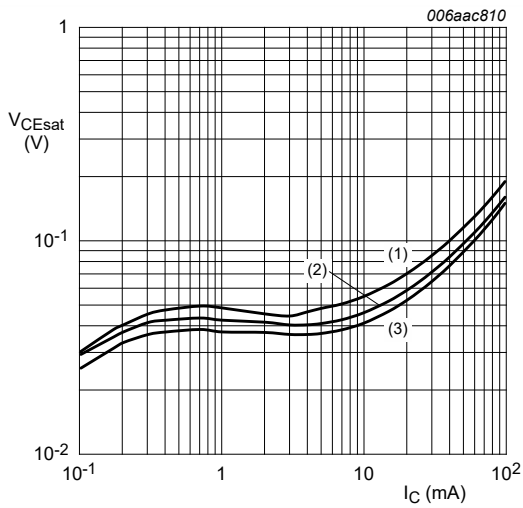
$V_{CE} = 5\text{ V}$
 (1) $T_{amb} = 100\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = -40\text{ °C}$

Fig. 3. NPN transistor: DC current gain as a function of collector current; typical values



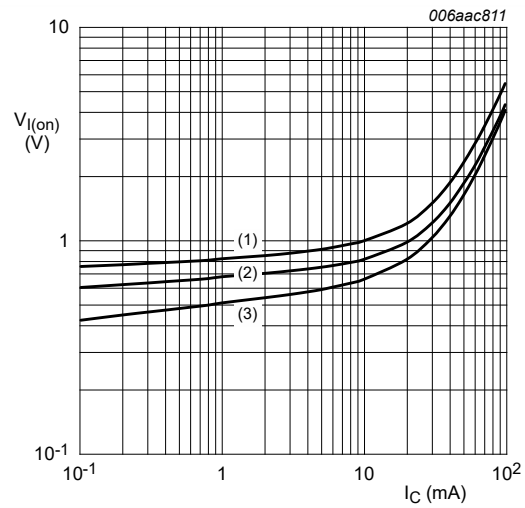
$T_{amb} = 25\text{ °C}$

Fig. 4. NPN transistor: Collector current as a function of collector-emitter voltage; typical values



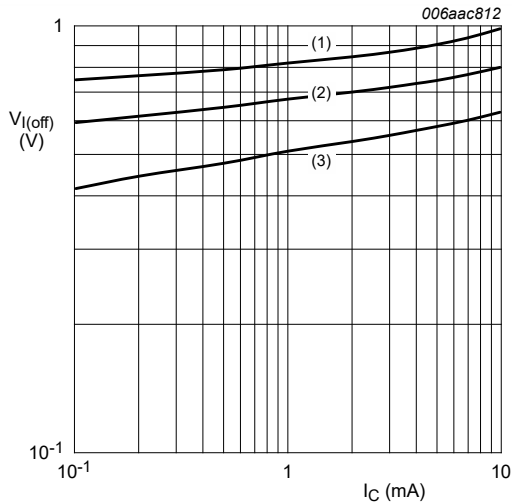
$I_C/I_B = 20$
 (1) $T_{amb} = 100\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = -40\text{ °C}$

Fig. 5. NPN transistor: Collector-emitter saturation voltage as a function of collector current; typical values



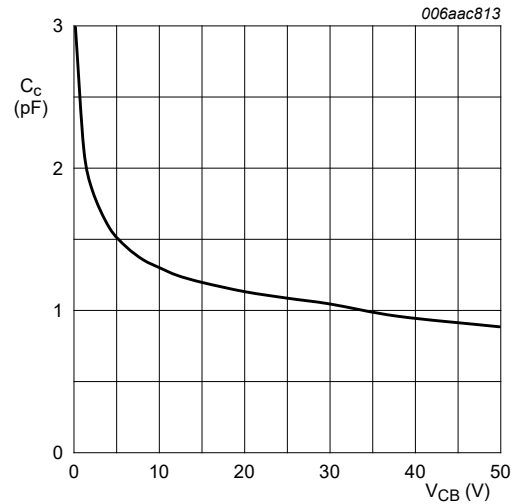
$V_{CE} = 0.3\text{ V}$
 (1) $T_{amb} = -40\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = 100\text{ °C}$

Fig. 6. NPN transistor: On-state input voltage as a function of collector current; typical values



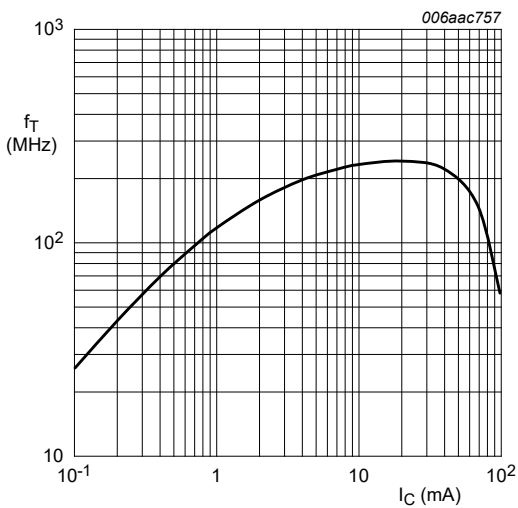
$V_{CE} = 5\text{ V}$
 (1) $T_{amb} = -40\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = 100\text{ °C}$

Fig. 7. NPN transistor: Off-state input voltage as a function of collector current; typical values



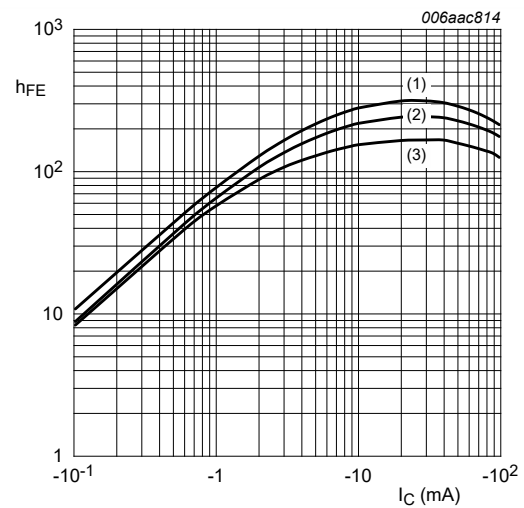
$f = 1\text{ MHz}$; $T_{amb} = 25\text{ °C}$

Fig. 8. NPN transistor: Collector capacitance as a function of collector-base voltage; typical values



$V_{CE} = 5\text{ V}$; $T_{amb} = 25\text{ °C}$

Fig. 9. NPN transistor: Transition frequency as a function of collector current; typical values of built-in transistor



$V_{CE} = -5\text{ V}$
 (1) $T_{amb} = 100\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = -40\text{ °C}$

Fig. 10. PNP transistor: DC current gain as a function of collector current; typical values

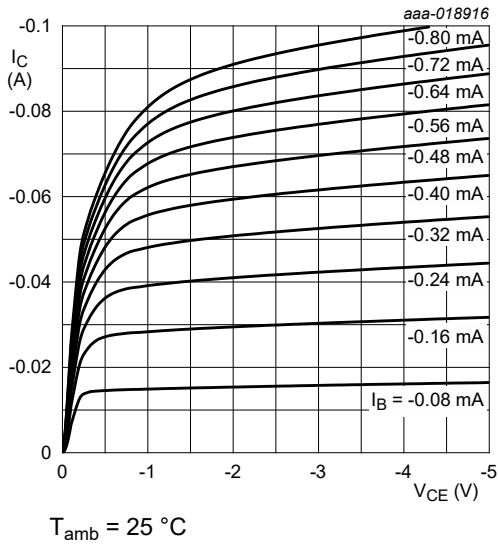


Fig. 11. PNP transistor: Collector current as a function of collector-emitter voltage; typical values

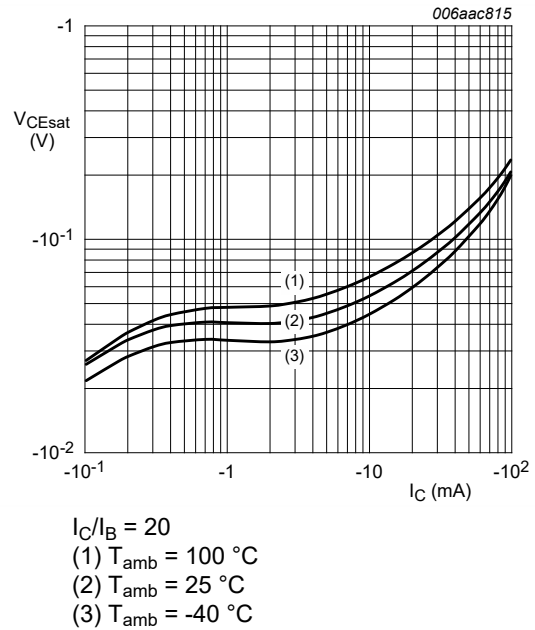


Fig. 12. PNP transistor: Collector-emitter saturation voltage as a function of collector current; typical values

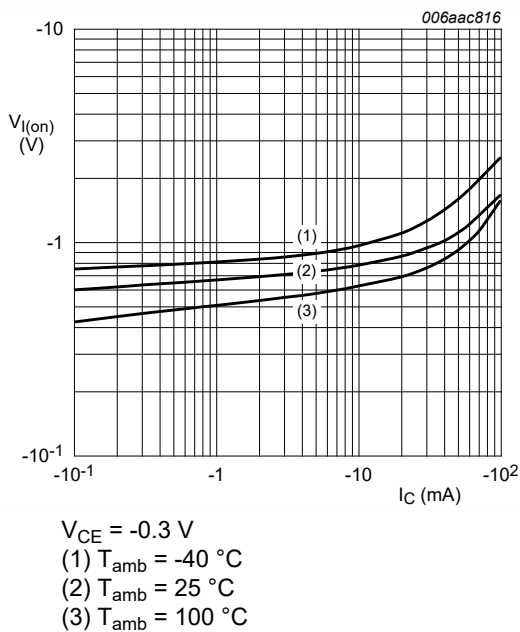


Fig. 13. PNP transistor: On-state input voltage as a function of collector current; typical values

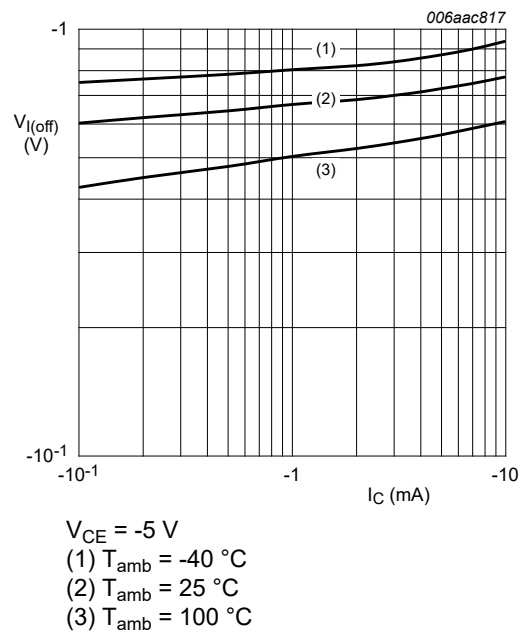
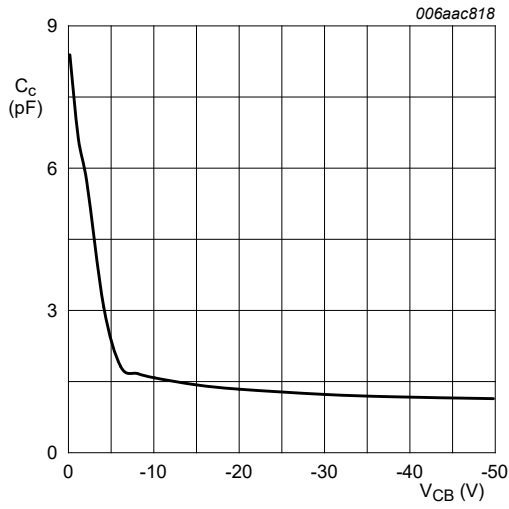
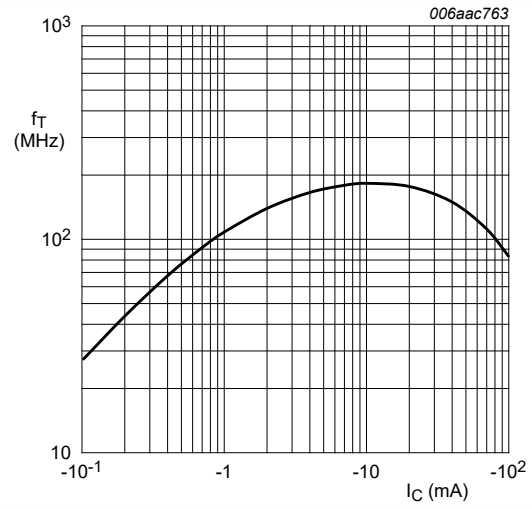


Fig. 14. PNP transistor: Off-state input voltage as a function of collector current; typical values



$f = 1 \text{ MHz}; T_{\text{amb}} = 25 \text{ }^\circ\text{C}$

Fig. 15. PNP transistor: Collector capacitance as a function of collector-base voltage; typical values



$V_{\text{CE}} = -5 \text{ V}; T_{\text{amb}} = 25 \text{ }^\circ\text{C}$

Fig. 16. PNP transistor: Transition frequency as a function of collector current; typical values of built-in transistor

11. Test information

Resistor calculation

- Calculation of bias resistor 1 (R1)

$$R_1 = \frac{V(I_2) - V(I_1)}{I_2 - I_1}$$

- Calculation of bias resistor ratio (R2/R1)

$$\frac{R_2}{R_1} = \frac{V(I_4) - V(I_3)}{R_1 \cdot (I_4 - I_3)} - 1$$

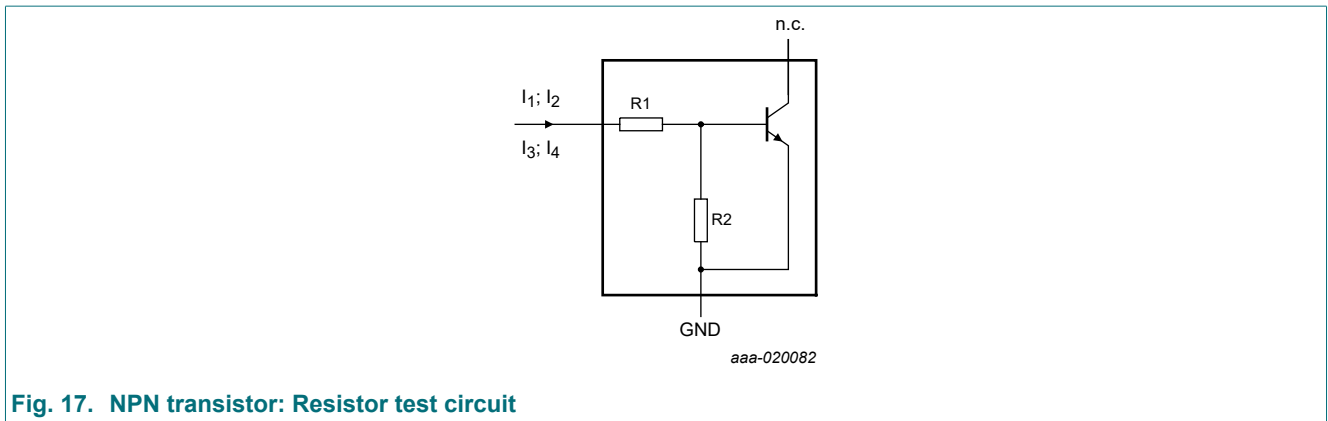


Fig. 17. NPN transistor: Resistor test circuit

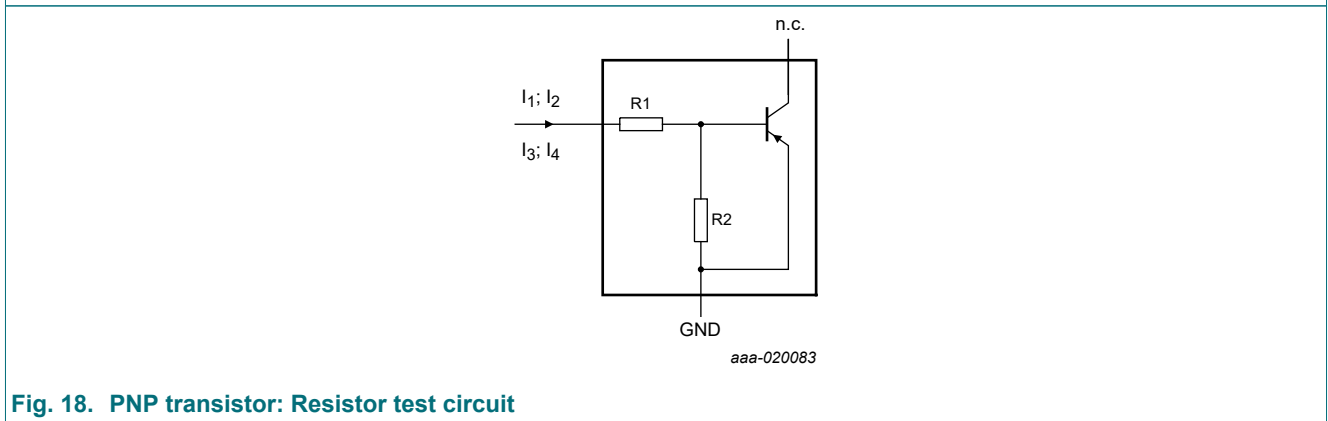


Fig. 18. PNP transistor: Resistor test circuit

Resistor test conditions

Table 8. Resistor test conditions

PUMD10	R1 (kΩ)	R2 (kΩ)	Test conditions			
			I ₁	I ₂	I ₃	I ₄
TR1 (NPN)	2.2	47	90 μA	140 μA	-55 μA	-105 μA
TR2 (PNP)	2.2	47	-90 μA	-140 μA	55 μA	105 μA

12. Package outline

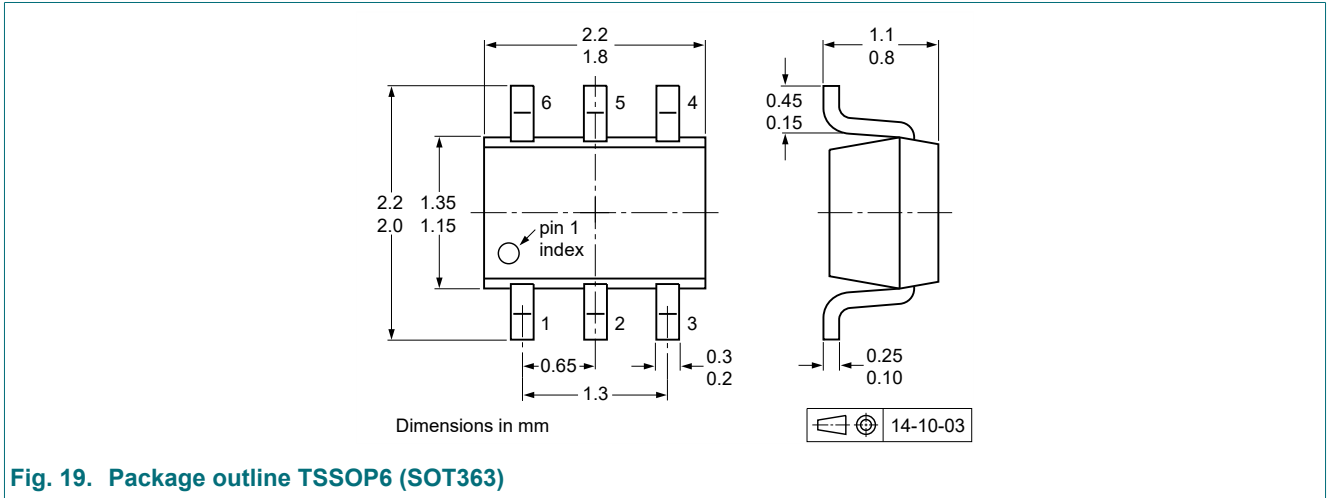


Fig. 19. Package outline TSSOP6 (SOT363)

13. Soldering

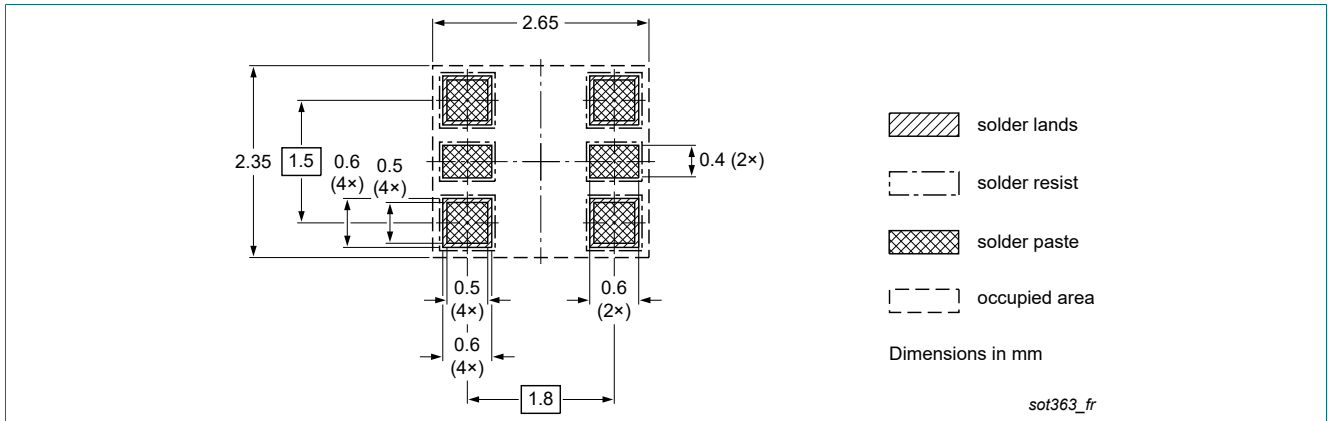


Fig. 20. Reflow soldering footprint for TSSOP6 (SOT363)

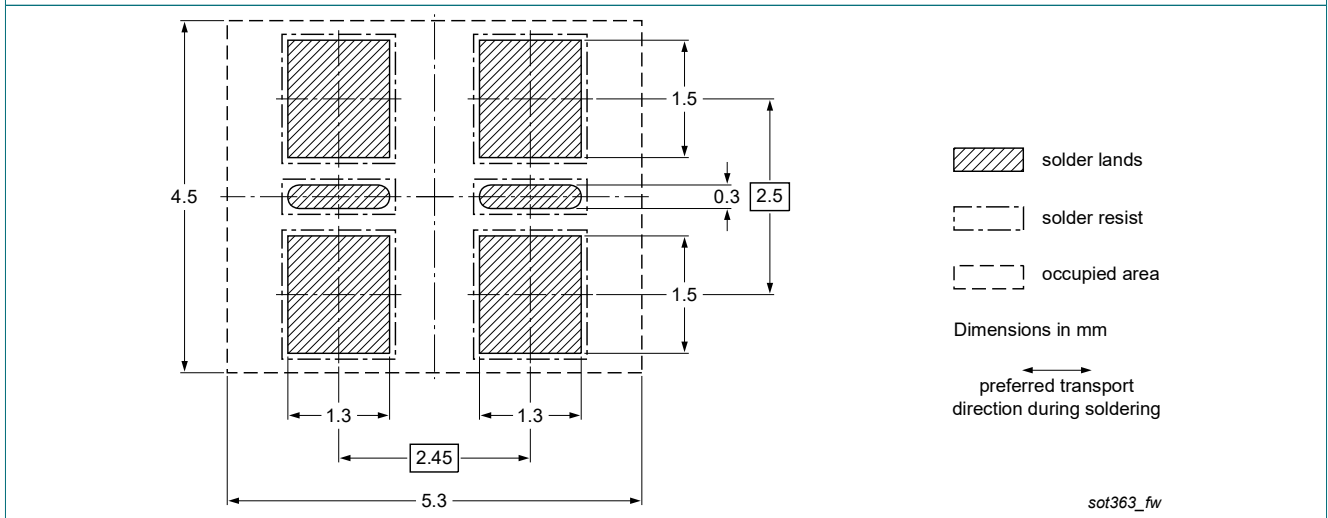


Fig. 21. Wave soldering footprint for TSSOP6 (SOT363)

14. Revision history

Table 9. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PUMD10 v.7	20221001	Product data sheet	-	PEMD10_PUMD10 v.6
Modifications:	<ul style="list-style-type: none"> The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia. Legal texts have been adapted to the new company name where appropriate. Family data sheet reduced to single type data sheet. Product changed to non-automotive qualification. Please refer to nexperia.com for automotive (-Q) product alternative(s). Packing information removed. 			
PEMD10_PUMD10 v.6	20120104	Product data sheet	-	PEMD10_PUMD10 v.5
PEMD10_PUMD10 v.5	20040415	Product data sheet	-	PEMD10_PUMD10 v.4
PEMD10_PUMD10 v.4	20031104	Product specification	-	PEMD10 v.2 PUMD10 v.3

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the internet at <https://www.nexperia.com>.

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